

Notice of References Cited	Application/Control No. 10/729,732	Applicant(s)/Patent Under Reexamination KAMAL ET AL.	
	Examiner Evan Pert	Art Unit 2826	Page 1 of 1

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★		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,872,609 B1	03-2005	Kamal et al.	438/194
	C	US-2003/0232507 A1	12-2003	Chen, Cheng Shun	438/763
	D	US-5,418,176	05-1995	Yang et al.	438/262
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	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

★		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

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	U	Mori et al., "ONO inter-poly dielectric scaling for nonvolatile memory applications", Feb. 1991, IEEE Transactions on Electron Devices, Vol. 38, Issue 2, pages 386-391.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.